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Kind regards,

Team Nexperia



600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor 24 June 2015 **Product data sheet** 

#### 1. **General description**

NPN high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV3160Z

#### 2. **Features and benefits**

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub> •

#### Applications 3.

- Electronic ballast for fluorecent lighting
- LED driver for LED chain module
- LCD backlighting
- HID front lighting •
- Hook switch for wired telecom •
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	600	V
I <sub>C</sub>	collector current		-	-	0.1	А





600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1-1
3	E	emitter		· •
4	С	collector	☐1	3 sym016

## 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PBHV2160Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PBHV2160Z	HV216Z

600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

#### **Limiting values** 8.

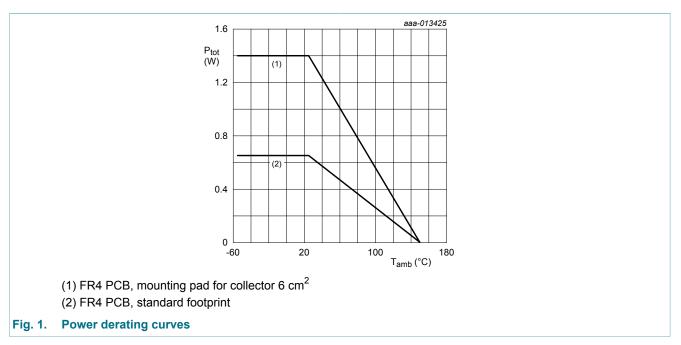
#### Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	600	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	600	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	600	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	0.1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



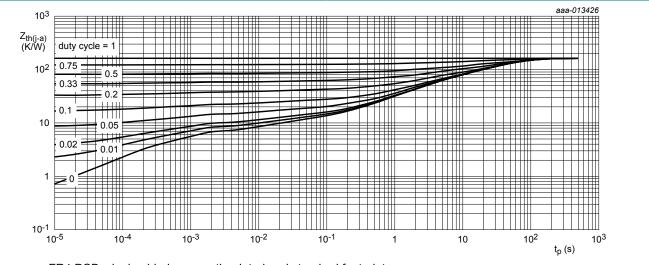
#### 600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

## 9. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	190	K/W
from junction to ambient		[2]	-	-	89	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

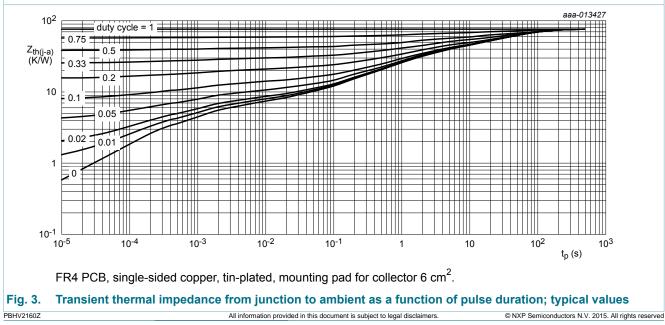
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



FR4 PCB, single-sided copper, tin-plated and standard footprint.

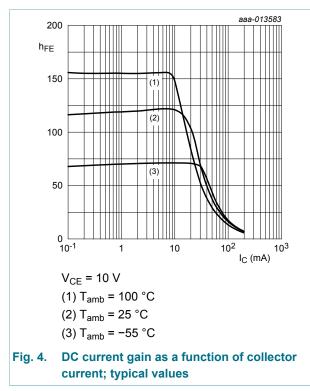


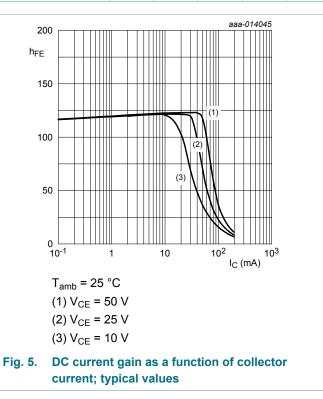


#### 600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

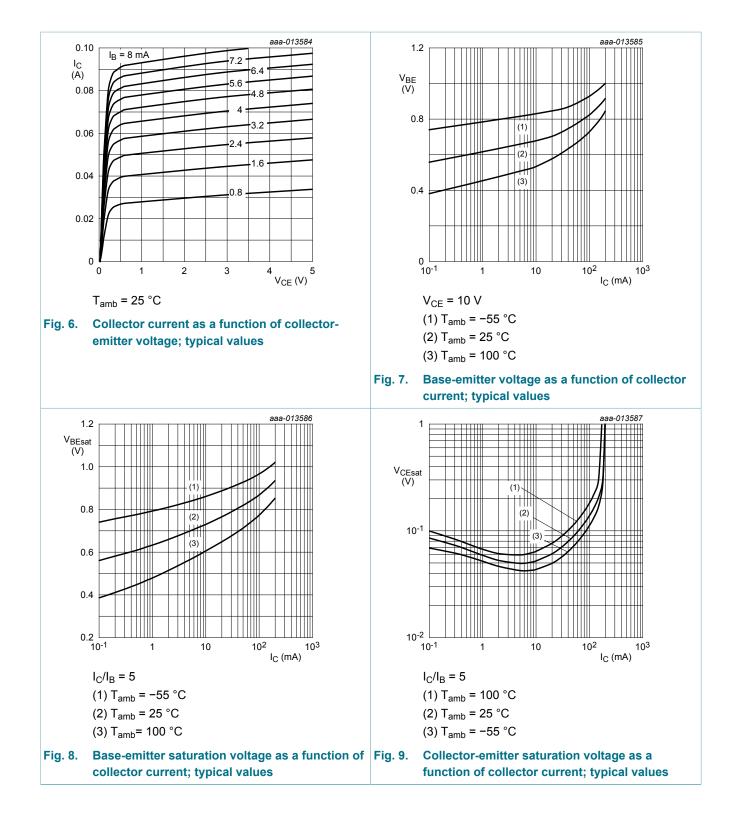
## **10. Characteristics**

Table 7. Ch	aracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = 400 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 400 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 400 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 4.8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	70	125	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 30 mA; $I_{B}$ = 6 mA; $T_{amb}$ = 25 °C	-	65	125	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 50 mA; $I_B$ = 5 mA; pulsed; $t_p \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-	950	mV
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	1.7	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = 0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	81	-	pF

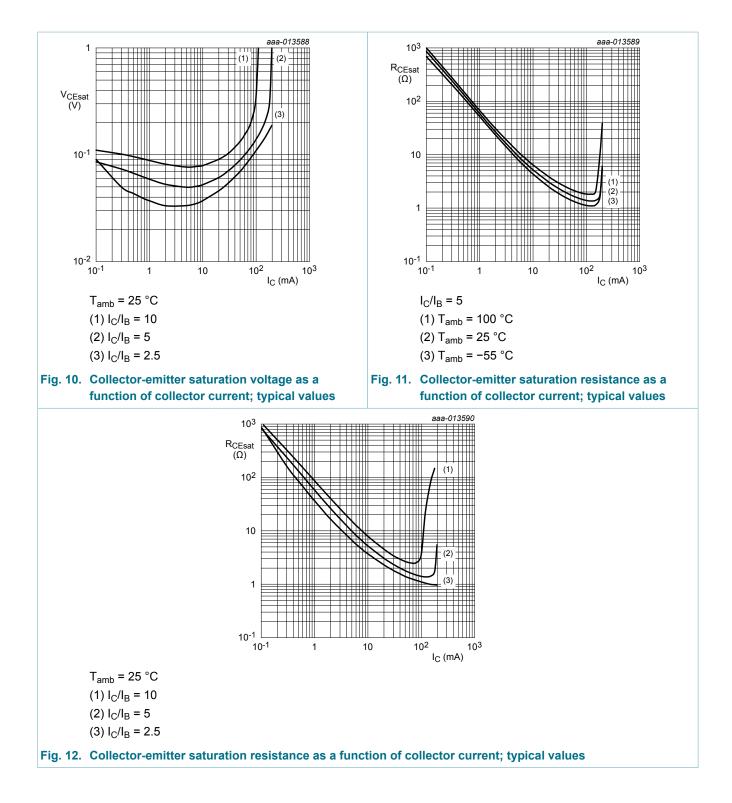




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#### 600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

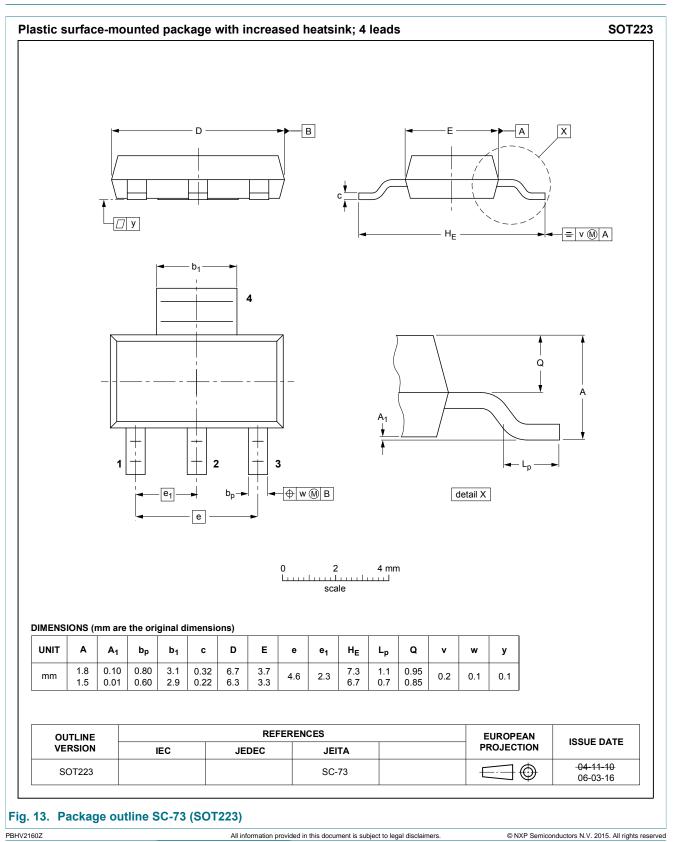


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600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

## 11. Package outline

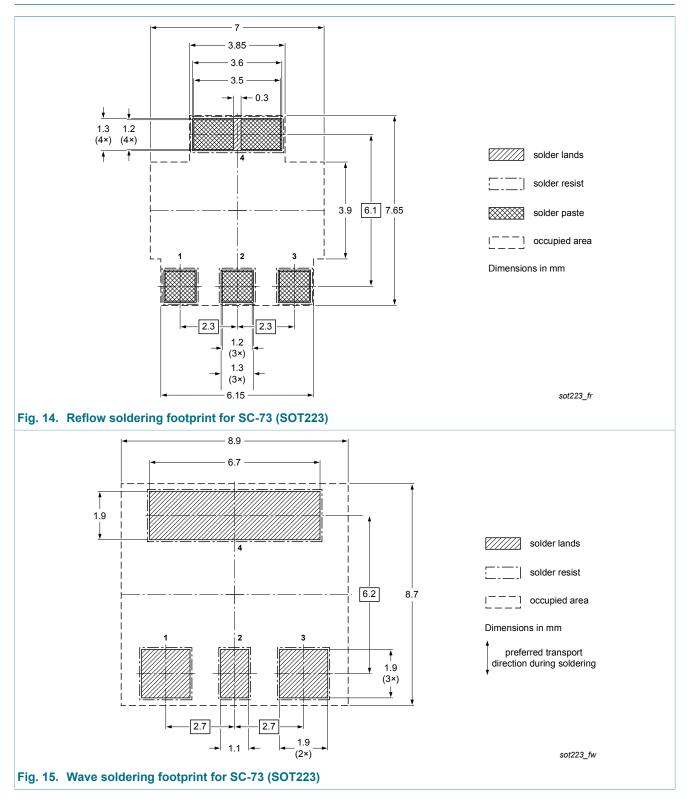


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**Product data sheet** 

600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

## 12. Soldering



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## **13. Revision history**

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV2160Z v.1	20150624	Product data sheet	-	-

#### 600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor

## 14. Legal information

#### 14.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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## **15. Contents**

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	5
10 11	Characteristics Package outline	
		8
11	Package outline	8 9
11 12	Package outline Soldering	8 9 10
11 12 13	Package outline Soldering Revision history Legal information Data sheet status	8 9 .10 .11 .11
11 12 13 14	Package outline Soldering Revision history Legal information Data sheet status Definitions	8 9 .10 .11 .11 .11
11 12 13 14 14.1	Package outline Soldering Revision history Legal information Data sheet status	8 9 .10 .11 .11 .11

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